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1. Field of the Invention The present invention relates to a plasma etching method and apparatus, and more particularly to a plasma etching method and apparatus capable of performing anisotropic etching on a material having an isotropic etching property such as, for example, a material having an isotropic etching property, such as an oxide film or the like, deposited on a silicon substrate.

2. Description of the Related Art In the conventional anisotropic etching method, a layer of a material to be etched is formed on a substrate, such as a semiconductor wafer, and is then processed by a reactive ion etching process using a gas mixture of a fluorine-containing compound (SF.sub.x) and an inert gas. An example of such conventional anisotropic etching method is shown in FIG. 6. In FIG. 6, reference numeral 201 designates a silicon substrate to be etched, and a resist film 202 is formed on the silicon substrate 201. The resist film 202 has an opening 202a. The silicon substrate 201 is then etched by plasma generated from a gas mixture of SF.sub.x and the inert gas by using, for example, a parallel plate type apparatus 203. During the etching, a gas pulse is applied to the gas mixture in accordance with a predetermined procedure so as to generate the plasma. During this etching, the gas mixture is passed through a nozzle 203a to be introduced into a chamber 203b of the parallel plate type apparatus 203. In the parallel plate type apparatus 203, parallel flat plates 203a and 203b, i.e., an upper plate 203a and a lower plate 203b, are arranged to face each other with a predetermined distance interposed therebetween. In a gap formed between the flat plates 203a and 203b, a plasma is generated by applying a high frequency voltage across the plates 203a and 203b. The gas mixture introduced into the chamber 203b through the nozzle 203a is heated by the high frequency voltage applied to 520fdb1ae7

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